

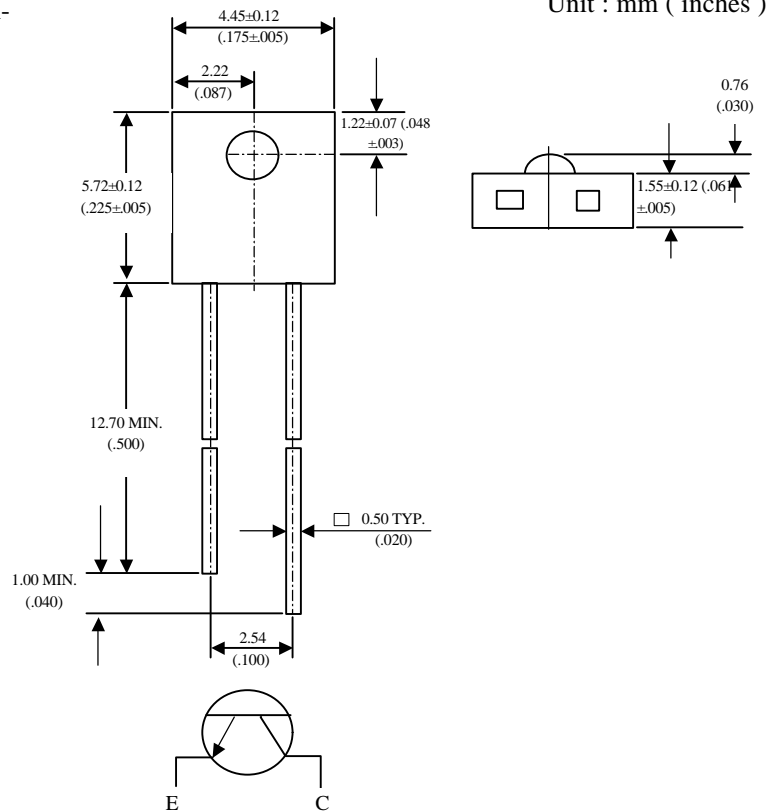
# SIDE LOOK PACKAGE NPN PHOTODETECTOR

## MID-11422

### Description

The MID-11422 is a NPN silicon phototransistor mounted in a lensed, water clear plastic and side looking package.

### Package Dimensions



Notes :

1. Tolerance is  $\pm 0.25\text{mm}$  (.010") unless otherwise noted .
2. Protruded resin under flange is 1.5 mm (.059") max
3. Lead spacing is measured where the leads emerge from the package.

### Absolute Maximum Ratings

@  $T_A=25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Collector-Emitter Voltage	30	V
Emitter-Collector Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

**UNI**

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## Optical-Electrical Characteristics

@ T<sub>A</sub>=25°C

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector-Emitter Breakdown Voltage	I <sub>e</sub> =0.1mA E <sub>e</sub> =0	V <sub>(BR)CEO</sub>	30			V
Emitter-Collector Breakdown Voltage	I <sub>e</sub> =0.1mA E <sub>e</sub> =0	V <sub>(BR)ECO</sub>	5			V
Collector-Emitter Saturation Voltage	I <sub>c</sub> =0.5 mA E <sub>e</sub> =0.1mW/cm <sup>2</sup>	V <sub>CE(SAT)</sub>			0.4	V
Rise Time	V <sub>R</sub> =30V, 0=1KΩ	T <sub>r</sub>		15		μS
Fall Time	I <sub>C</sub> =1mA	T <sub>f</sub>		15		
Collector Dark Current	V <sub>CE</sub> =10V E <sub>e</sub> =0mW/cm <sup>2</sup>	I <sub>CEO</sub>			100	nA
On State Collector Current	V <sub>CE</sub> =5V E <sub>e</sub> =0.1mW/cm <sup>2</sup>	I <sub>C(ON)</sub>	0.256			mA

## Typical Optical-Electrical Characteristic Curves

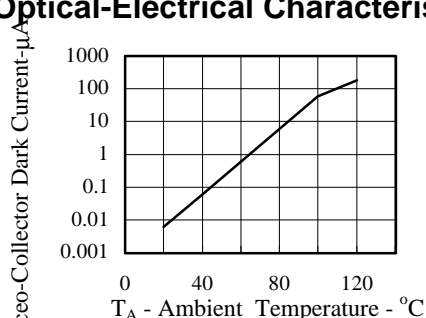


FIG.1 COLLECTOR DARK CURRENT VS AMBIENT TEMPERATURE

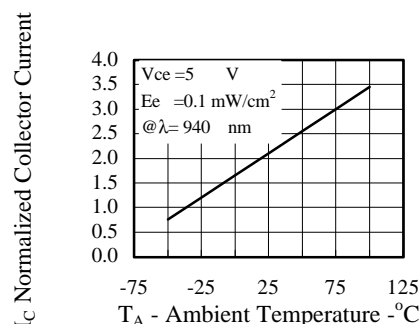


FIG.2 NORMALIZED COLLECTOR CURRENT VS AMBIENT TEMPERATURE

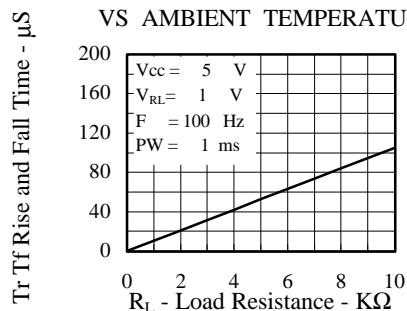


FIG.3 RISE AND FALL TIME VS LOAD RESISTANCE

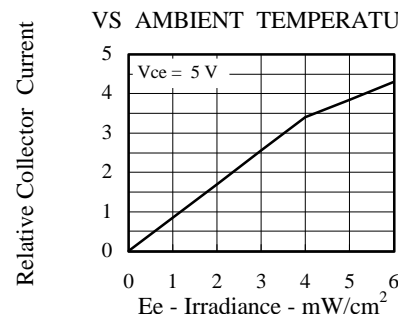


FIG.4 RELATIVE COLLECTOR CURRENT VS IRRADIANCE

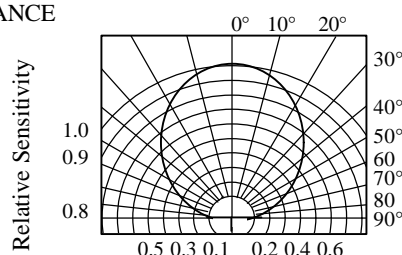


FIG.5 SENSITIVITY DIAGRAM